

APPLICTIONS

Unit

mA

mA

nA

Unit
V

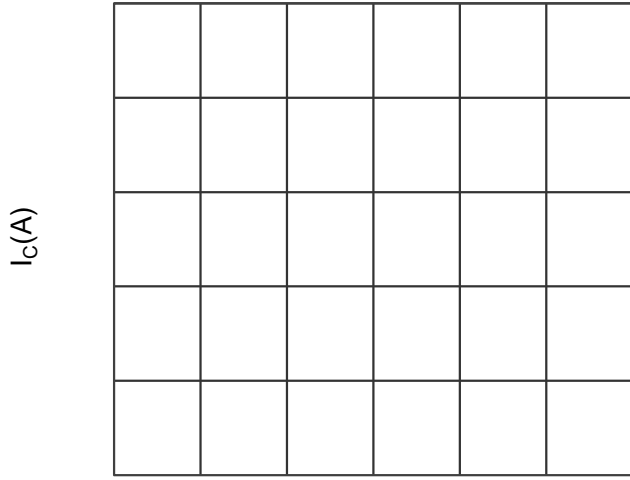
Diode-RECTIERV

Unit
V
V
 μ A
mA
K/W

R

$V_R=1600V, T_R=25$

1



V_{GE} V
Figure 3. Typical Transfer characteristics IGBT-inverter

$E_{on}E_{off}(mJ)$

R_g Ω
Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

(mJ)

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Figure 10. Transient Thermal Impedance of Diode and IGBT-inverter

MMG25H120XT6TC

Figure 15. Circuit Diagram